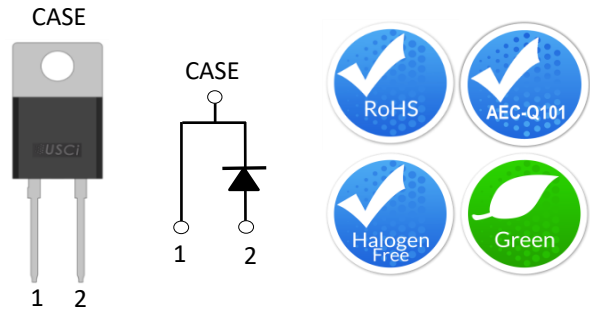


Description

United Silicon Carbide, Inc. offers the 3rd generation of high performance SiC Merged-PiN-Schottky (MPS) diodes. With zero reverse recovery charge and 175°C maximum junction temperature, these diodes are ideally suited for high frequency and high efficiency power systems with minimum cooling requirements.



Part Number	Package	Marking
UJ3D06506TS	TO-220-2L	UJ3D06506TS

Features

- ◆ 175°C maximum operating junction temperature
- ◆ Easy paralleling
- ◆ Extremely fast switching not dependent on temperature
- ◆ No reverse or forward recovery
- ◆ Enhanced surge current capability, MPS structure
- ◆ Excellent thermal performance, Ag sintered
- ◆ 100% UIS tested
- ◆ AEC-Q101 qualified

Typical Applications

- ◆ Power converters
- ◆ Industrial motor drives
- ◆ Switching-mode power supplies
- ◆ Power factor correction modules

Maximum Ratings

Parameter	Symbol	Test Conditions	Value	Units
DC blocking voltage	V_R		650	V
Repetitive peak reverse voltage, $T_J=25^\circ\text{C}$	V_{RRM}		650	V
Surge peak reverse voltage	V_{RSM}		650	V
Maximum DC forward current	I_F	$T_C = 153^\circ\text{C}$	6	A
Non-repetitive forward surge current sine halfwave	I_{FSM}	$T_C = 25^\circ\text{C}, t_p = 10\text{ms}$	45	A
		$T_C = 110^\circ\text{C}, t_p = 10\text{ms}$	39	
Repetitive forward surge current sine halfwave, $D=0.1$	I_{FRM}	$T_C = 25^\circ\text{C}, t_p = 10\text{ms}$	29.5	A
		$T_C = 110^\circ\text{C}, t_p = 10\text{ms}$	17.9	
Non-repetitive peak forward current	$I_{F,max}$	$T_C = 25^\circ\text{C}, t_p = 10\mu\text{s}$	320	A
		$T_C = 110^\circ\text{C}, t_p = 10\mu\text{s}$	320	
i^2t value	$\int i^2 dt$	$T_C = 25^\circ\text{C}, t_p = 10\text{ms}$	10.1	A ² s
		$T_C = 110^\circ\text{C}, t_p = 10\text{ms}$	7.6	
Power dissipation	P_{Tot}	$T_C = 25^\circ\text{C}$	93.4	W
		$T_C = 153^\circ\text{C}$	13.4	
Maximum junction temperature	$T_{J,max}$		175	°C
Operating and storage temperature	T_J, T_{STG}		-55 to 175	°C
Soldering temperatures, wavesoldering only allowed at leads	T_{sold}	1.6mm from case for 10s	260	°C

Electrical Characteristics

$T_J = +25^\circ\text{C}$ unless otherwise specified

Parameter	Symbol	Test Conditions	Value			Units
			Min	Typ	Max	
Forward voltage	V_F	$I_F=6\text{A}, T_J=25^\circ\text{C}$	-	1.5	1.7	V
		$I_F=6\text{A}, T_J=150^\circ\text{C}$	-	1.8	2.1	
		$I_F=6\text{A}, T_J=175^\circ\text{C}$	-	1.9	2.25	
Reverse current	I_R	$V_R=650\text{V}, T_J=25^\circ\text{C}$	-	0.7	40	μA
		$V_R=650\text{V}, T_J=175^\circ\text{C}$	-	6		
Total capacitive charge ⁽¹⁾	Q_C	$V_R=400\text{V}$		14.5		nC
Total capacitance	C	$V_R=1\text{V}, f=1\text{MHz}$		196		pF
		$V_R=300\text{V}, f=1\text{MHz}$		24		
		$V_R=600\text{V}, f=1\text{MHz}$		21		
Capacitance stored energy	E_C	$V_R=400\text{V}$		2.2		μJ

(1) Q_C is independent on T_J , di_F/dt , and I_F as shown in the application note USCi_AN0011.

Thermal characteristics

Parameter	symbol	Test Conditions	Value			Units
			Min	Typ	Max	
Thermal resistance, junction - case	$R_{\theta JC}$			1.2	1.6	$^\circ\text{C}/\text{W}$

Typical Performance

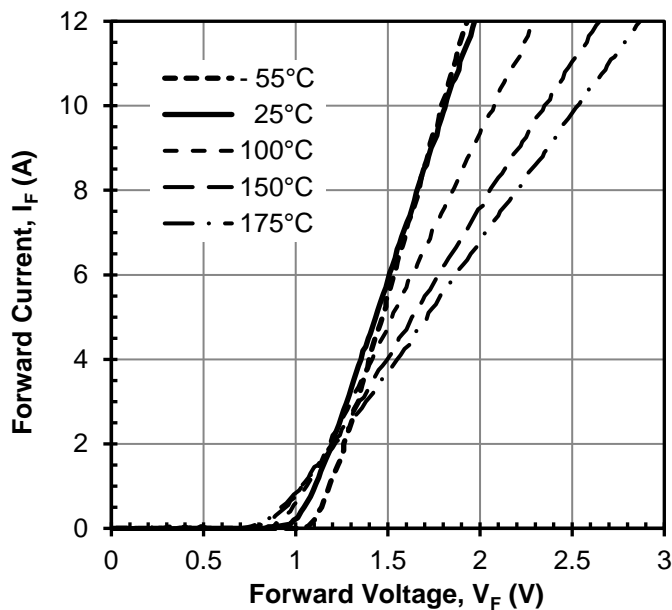


Figure 1 Typical forward characteristics

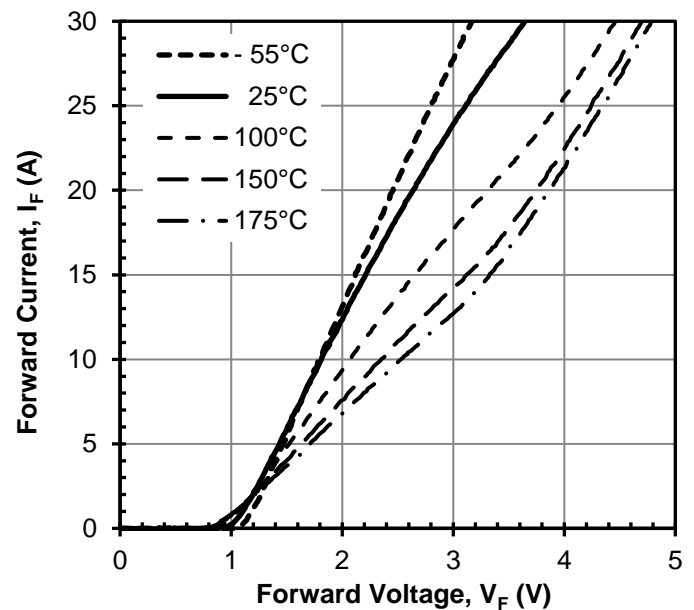


Figure 2 Typical forward characteristics in surge current

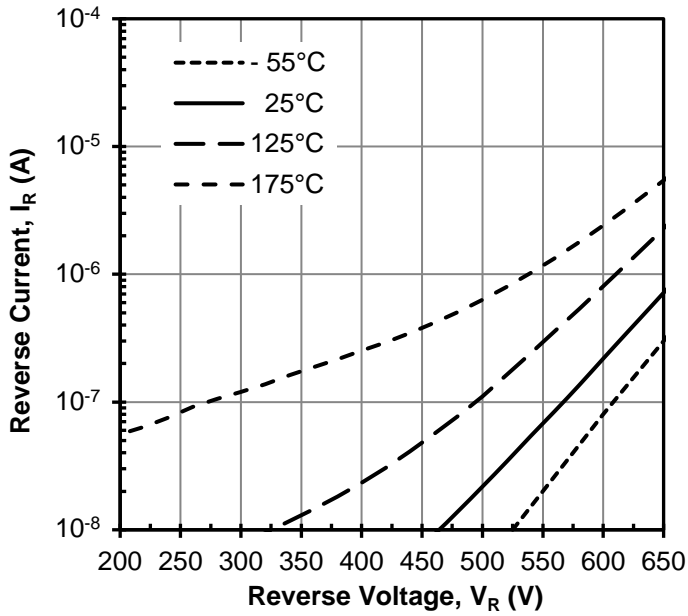


Figure 3 Typical reverse characteristics

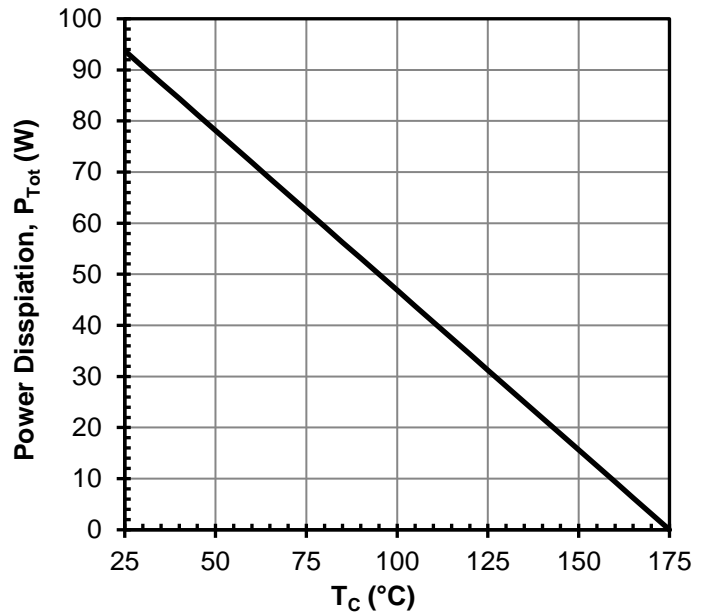


Figure 4 Power dissipation

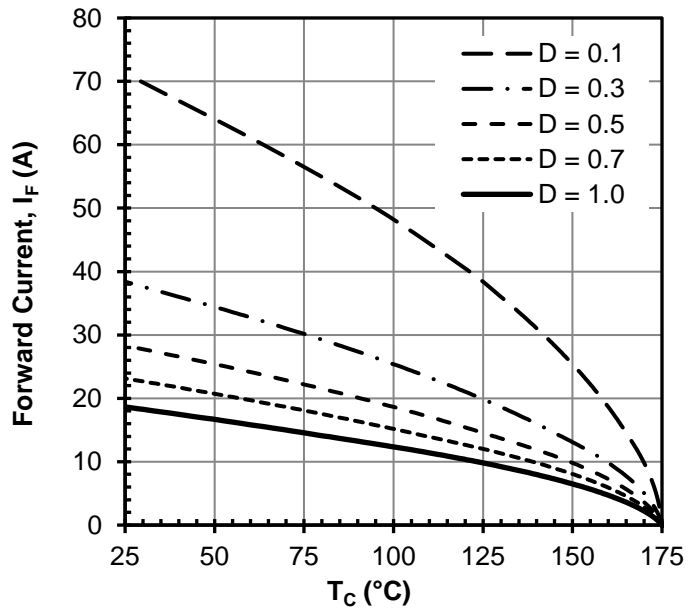


Figure 5 Diode forward current

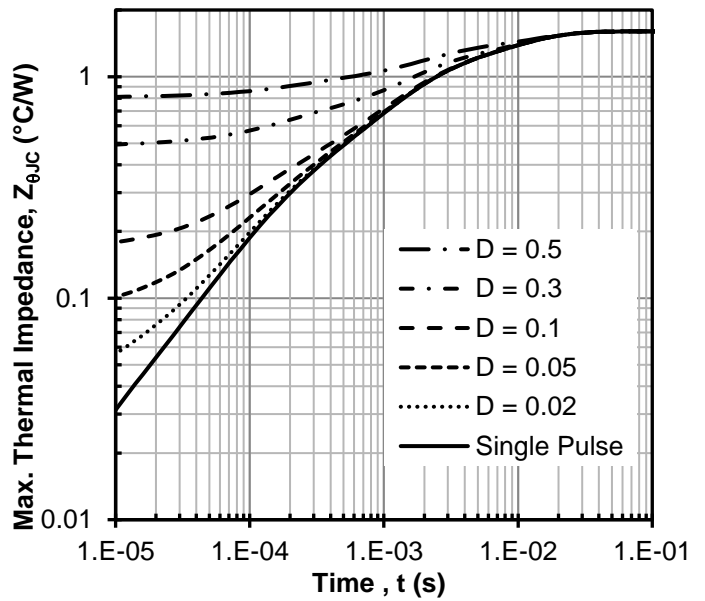


Figure 6 Maximum transient thermal impedance

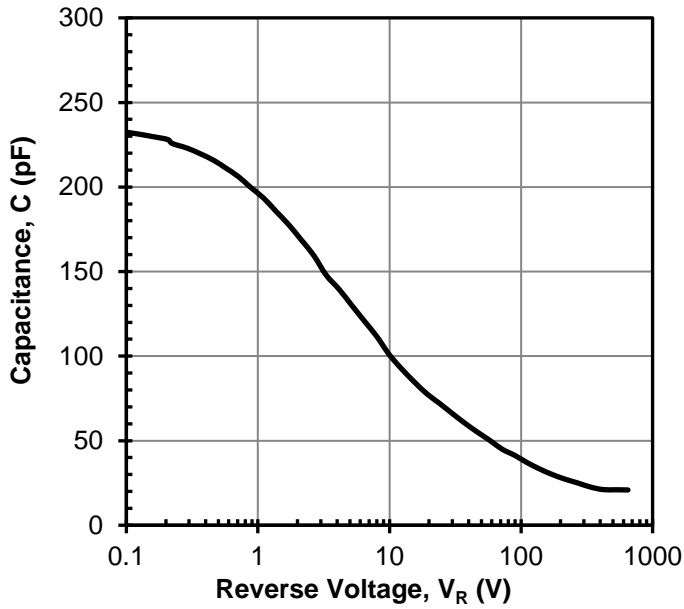


Figure 7 Capacitance vs. reverse voltage at 1MHz

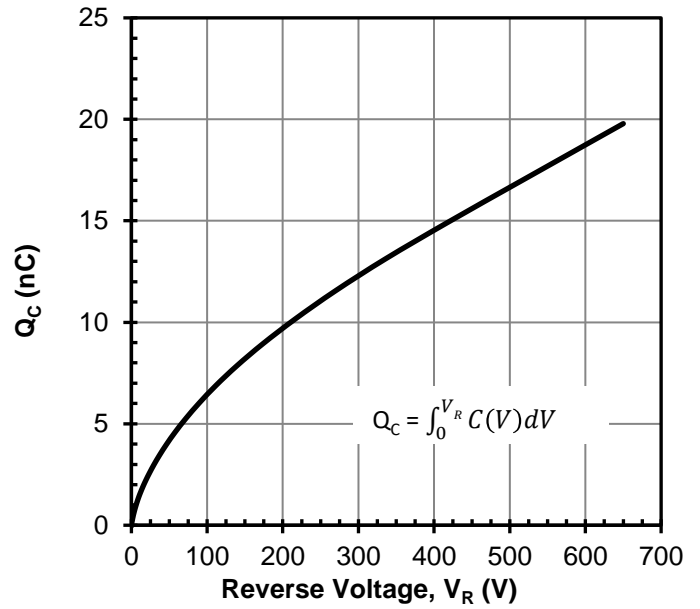


Figure 8 Typical capacitive charge vs. reverse voltage

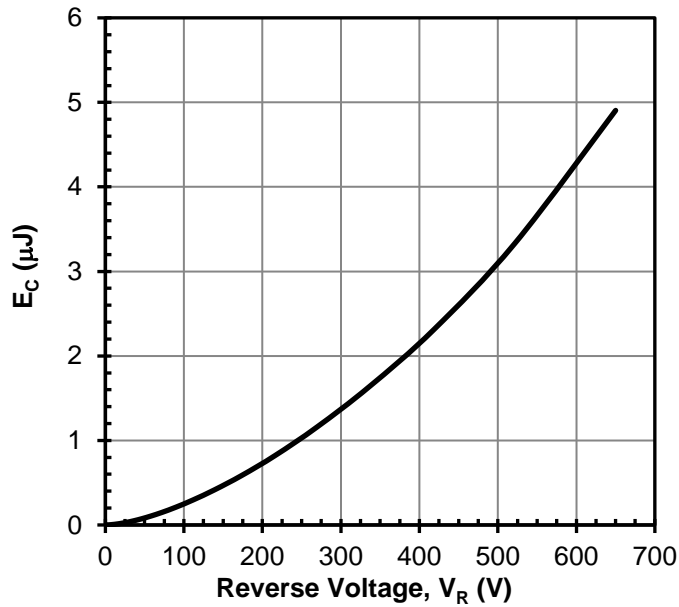


Figure 9 Typical capacitance stored energy vs. reverse voltage